



# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

BAS70WS

## SOD-323 Schottky Barrier Diode 肖特基势垒二极管

### Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	BAS70WS	
Pin 管脚		
Mark 打标	K73	

### Absolute Maximum Ratings 最大额定值

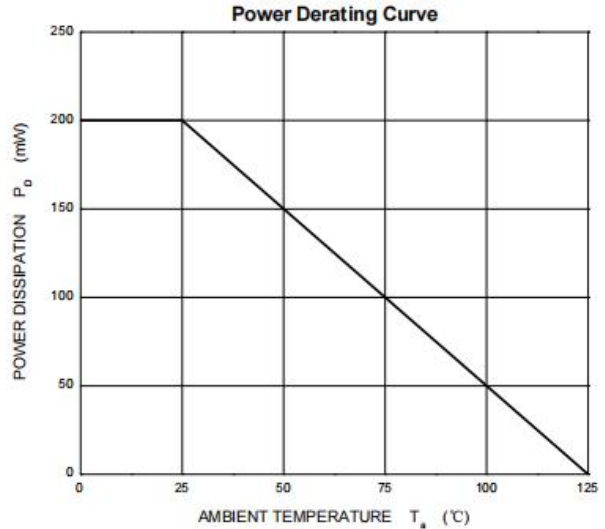
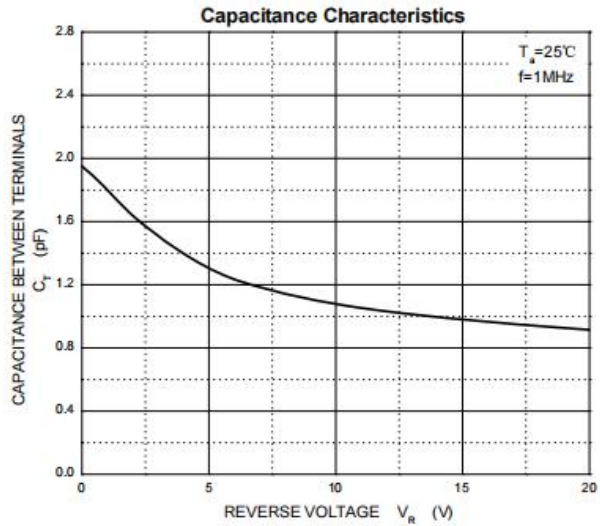
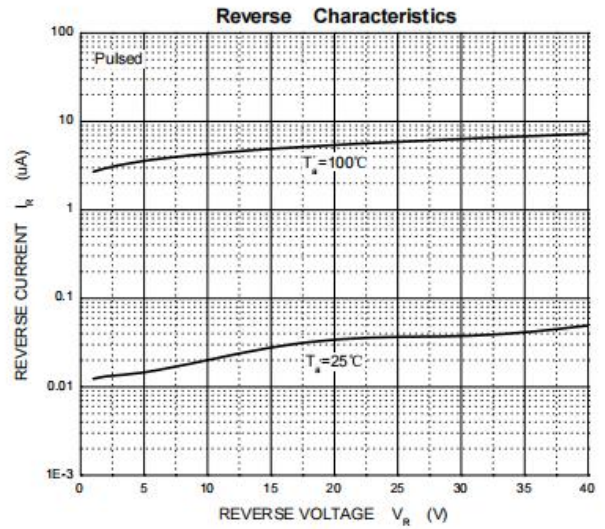
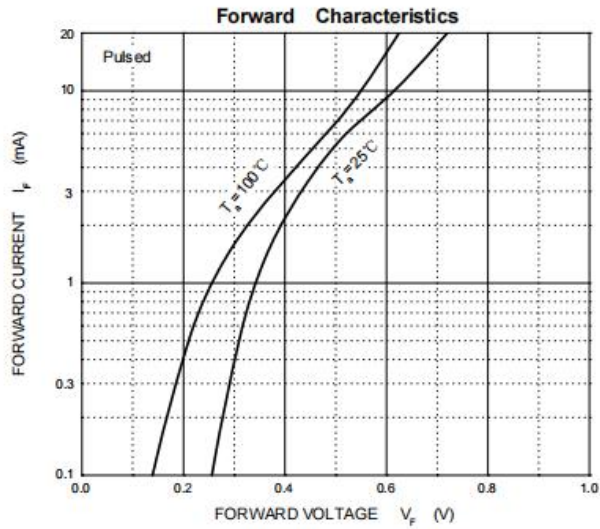
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	$V_{RRM}$	70	V
Reverse Work Voltage 反向工作电压	$V_{RWM}$		
DC Reverse Voltage 直流反向电压	$V_R$		
Forward Work Current 正向工作电流	$I_F(I_O)$	70	mA
Peak Forward Surge Current 正向峰值浪涌电流	$I_{FSM}$	100	mA
Power dissipation 耗散功率	$P_D(T_a=25^\circ C)$	200	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	500	$^\circ C/W$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	-55to+125 $^\circ C$	

### Electrical Characteristics 电特性

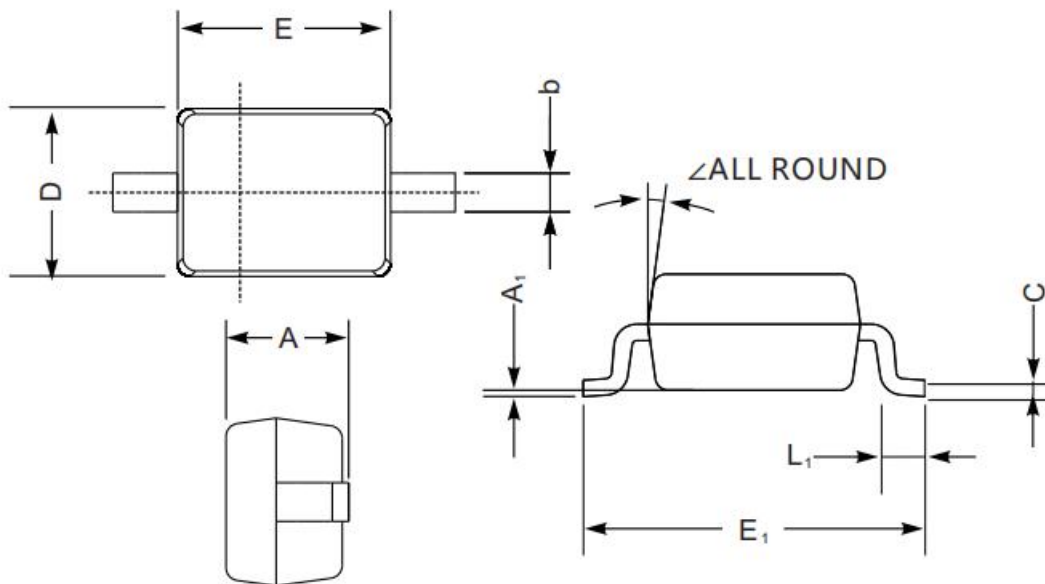
( $T_A=25^\circ C$  unless otherwise noted 如无特殊说明, 温度为  $25^\circ C$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压( $I_R=10\mu A$ )	$V_{(BR)}$	70	—	V
Reverse Leakage Current 反向漏电流( $V_R=50V$ )	$I_R$	—	0.1	$\mu A$
Forward Voltage( $I_F=1mA$ ) 正向电压( $I_F=15mA$ )	$V_F$		0.41 1	V
Diode Capacitance 二极管电容( $V_R=0V, f=1MHz$ )	$C_D$	—	2	pF
Reverse Recovery Time 反向恢复时间 ( $I_F=I_R=10mA, I_{rr}=0.1I_{IR}, R_L=100\Omega$ )	$T_{rr}$	—	5	nS

## ■ Typical Characteristic Curve 典型特性曲线



## ■Dimension 外形封装尺寸



SOD-323 mechanical data

UNIT		A	C	D	E	E <sub>1</sub>	b	L <sub>1</sub>	A <sub>1</sub>	$\angle$
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2	9°
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—	
mil	max	43	5.9	55	70	108	16	16	8	
	min	32	3.1	47	63	100	9.8	7.9	—	